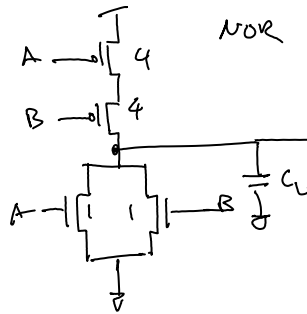
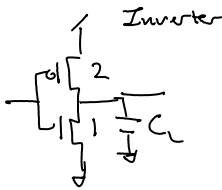
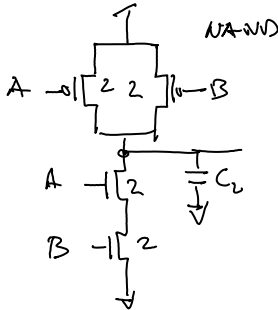


Logical Effort

Friday, March 05, 2010
08:57

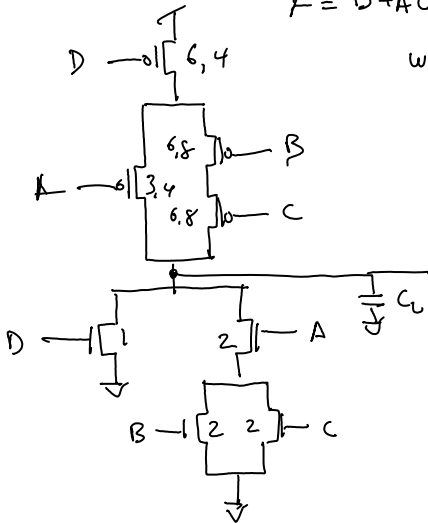
CMOS Logic

worst-case t_{pHL}, t_{pHL}

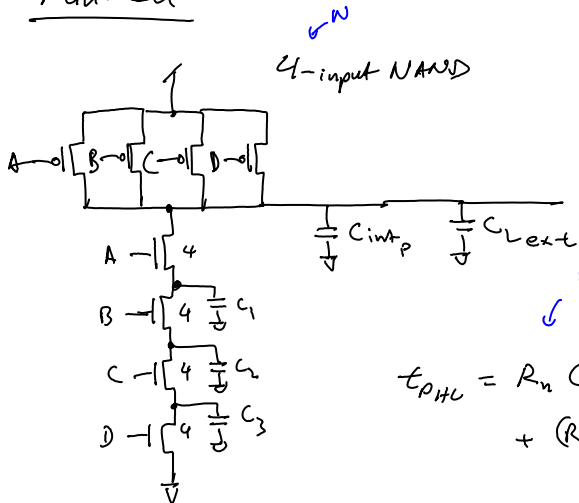


$$F = \overline{D + A(B+C)}$$

which sizing is better, and why?



Fan-In



$\frac{1}{4}$ of the R_n of an inverter

$$t_{pHL} = R_n C_3 + (R_n + R_n) C_2 + (R_n + R_n + R_n) C_1 + (R_n + R_n + R_n + R_n) (C_L + C_{int,p})$$

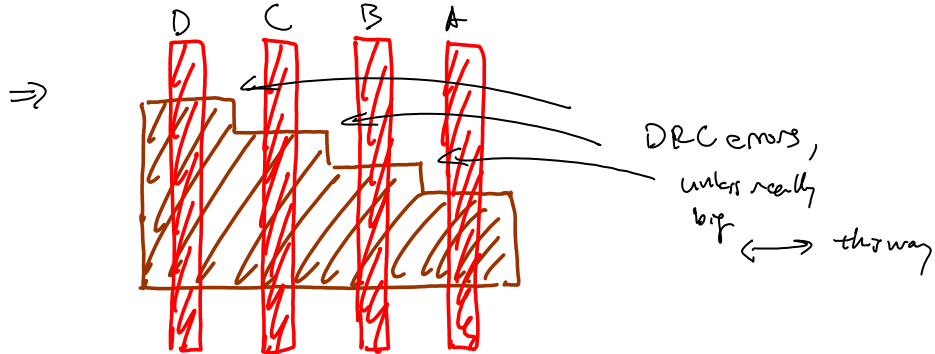
$\propto N$

$N \cdot C_{db,pmos}$

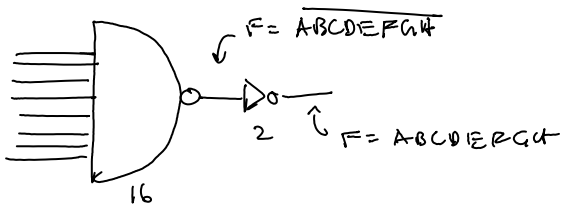
$$\Rightarrow t_{pHL} \propto N$$

you could size things differently, like make
 $D \rightarrow$ the biggest and $A \rightarrow$ the smallest

$$M_D > M_C > M_B > M_A$$

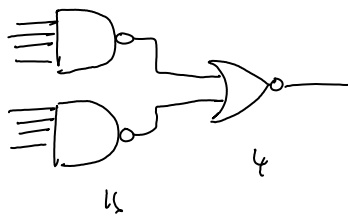


We could also make use of knowledge about the last incoming signal:



Breaking Up Gates

OR



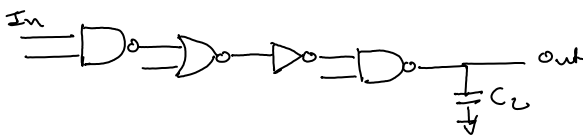
or, you could reduce the output swing and let the restoring effect of the inverter fix it.

Logical Effort

for an inverter

$$t_p = t_{p0} \left(1 + \frac{f}{\gamma} \right)$$

$$= 0.69 R_{inv} (C_{int} + C_{ext})$$



$$t_{NAND} = 0.69 R_{NAND} (C_{int, NAND} + C_{ext})$$

$$= 0.69 R_{NAND} C_{int, NAND} + 0.69 R_{NAND} \cdot C_{gate, NAND} \left(\frac{C_{ext}}{C_{gate, NAND}} \right)$$

fanout of NAND

$$t_{NAND} = 0.69 R_{NAND} C_{int, NAND} + 0.69 R_{NAND} C_{gate, NAND} \cdot C_{ext}$$

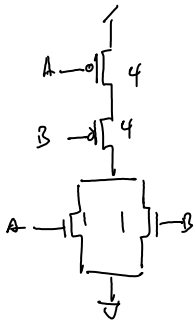
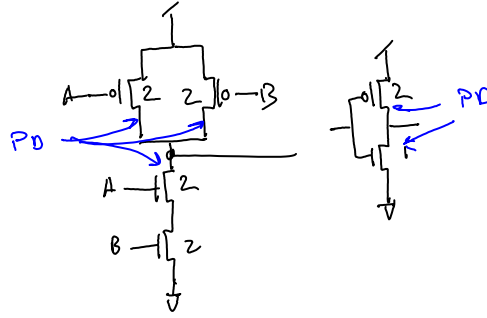
$$\frac{t_{NAND}}{t_{inv}} = \frac{0.69 R_{on} C_{int, NAND}}{0.69 R_{inv} C_{g, inv}} + \frac{0.69 R_{on} C_{gate, NAND}}{0.69 R_{inv} C_{g, inv}} \rightarrow \frac{C_{ext}}{C_{g, NAND}} \rightarrow \frac{C_{ext}}{R_{on} C_{g, NAND}}$$

$$D_{NAND} = \frac{t_{NAND}}{t_{inv}} = \underbrace{\frac{C_{int, NAND}}{C_{gate, inv}}}_{\text{parasitic delay}} + \underbrace{\frac{C_{gate, NAND}}{C_{gate, inv}}}_{\text{logical effort}} F_{O_{NAND}}$$

$$D_{NAND} = PD_{NAND} + LE_{NAND} F_{O_{NAND}}$$

$$LE_{2NAND} = \frac{2+2}{2+1} = \frac{4}{3}$$

$$PD_{2NAND} = \frac{2+2+2}{2+1} = 2$$



$$LE_{2NOR} = \frac{4+1}{2+1} = \frac{5}{3}$$

$$PD_{2NOR} = \frac{4+1+1}{2+1} = 2$$

$$LE_{N-NAND} = \frac{2N+1}{3}$$